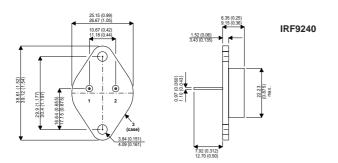
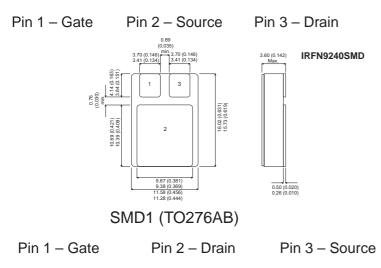


MECHANICAL DATA Dimensions in mm (inches)

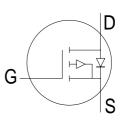


TO-3 Package (TO-204AA)



## IRF9240 IRFN9240SMD





### FEATURES

- P-CHANNEL POWER MOSFET
- HIGH VOLTAGE
- INTEGRAL PROTECTION DIODE
- AVAILABLE IN TO-3 (TO-204AA) AND CERAMIC SURFACE MOUNT SMD1 (TO276AB)PACKAGE
  - **Note:** IRF9240SMD also available with pins 1 and 3 reversed on SMD 1 package.

#### **ABSOLUTE MAXIMUM RATINGS** (T<sub>case</sub> = 25°C unless otherwise stated)

			,
V <sub>DSS</sub>	Drain – Source Voltage		-200V
V <sub>DGR</sub>	Drain – Gate Voltage (R <sub>GS</sub> = 20KΩ)		–200V
V <sub>GS</sub>	Gate – Source Voltage	Gate – Source Voltage	
I <sub>D</sub>	Continuous Drain Current	@ T <sub>case</sub> = 25°C	-11A
		@ T <sub>case</sub> = 100°C	-7.0A
I <sub>DM</sub>	Pulsed Drain Current		-44A
P <sub>D</sub>	Max. Power Dissipation	@ T <sub>case</sub> = 25°C	125W
	Linear Derating Factor		1W / °C
т <sub>і</sub>	Operating Junction and		EE to 150°C
T <sub>stg</sub>	Storage Temperature Range		–55 to 150°C

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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# IRF9240 IRFN9240SMD

## **ELECTRICAL RATINGS** (T<sub>case</sub> = 25°C unless otherwise stated)

	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain – Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = -1mA$	-200			V
V <sub>GS(TH)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	-2		-4	V
I <sub>GSS</sub>	Gate – Source Leakage Current (forward)	V <sub>GS</sub> = -20V			-100	nA
	Gate – Source Leakage Current (reverse)	V <sub>GS</sub> = 20V			100	nA
I <sub>DSS</sub>		$V_{DS} = -160V$ , $V_{GS} = 0V$			-25	μA
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -160V			-1	mA
		$V_{GS} = 0V$ , $T_{case} = 125^{\circ}C$			-1	
I <sub>D(ON)</sub>	On State Drain Current <sup>1</sup>	$V_{DS} > I_{D(ON)} \times R_{DS(ON)} Max$	11			A
		$V_{GS} = -10V$	-11			A
R <sub>DS(ON)</sub>	Static Drain – Source On-State Resistance	$V_{GS} = -10V$ , $I_D = -7A$		0.35	0.5	Ω
	Forward Transconductance <sup>1</sup>	$V_{DS} > I_{D(ON)} \times R_{DS(ON)} Max$	4	6		S
9 <sub>fs</sub>		$I_D = -6A$	4	0		
C <sub>iss</sub>	Input capacitance	$V_{GS} = 0V$		1200		
C <sub>oss</sub>	Output capacitance	$V_{DS} = -25V$		570		pF
C <sub>rss</sub>	Reverse transfer capacitance	f = 1MHz		81		1
Qg	Total Gate Charge	V <sub>GS</sub> = -10V	28		60	
Q <sub>gs</sub>	Gate – Source Charge	$I_D = -11A$	3.0		15	nC
Q <sub>gd</sub>	Gate – Drain ("Miller") Charge	V <sub>DS</sub> = -100V	4.5		38	1
t <sub>d(on)</sub>	Turn-on Delay Time	$V_{DD} = -100V$ $I_{D} = -11A$ $Z_{O} = 9.1\Omega$			35	
t <sub>r</sub>	Rise Time				85	- ns
t <sub>d(off)</sub>	Turn-off Delay Time				85	
t <sub>f</sub>	Fall Time				65	
L <sub>D</sub>	Internal Drain Inductance			5.0		nH
L <sub>S</sub>	Internal Source Inductance			12.5		nH
HERMAL	CHARACTERISTICS	•				
	Characteristic		Min.	Тур.	Max.	Uni

		IVIII.	Typ.	IVIAA.	Unit
R <sub>θJC</sub>	Junction to Case			1.0	°C/W
R <sub>θJA</sub>	Junction to Ambient (TO-3 package	e only)		30	°C/W
ΤL	Max. Lead Temperature 0.063" from case for 10 sec. (TO-3 package	e only)	300		°C

#### SOURCE – DRAIN DIODE RATINGS AND CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
۱ <sub>S</sub>	Continuous Source Current (Body Diode)				-11	Α
I <sub>SM</sub>	Pulsed Source Current <sup>1</sup> (Body Diode)				-44	
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	$V_{GS} = 0V$ , $I_S = -11A$ $T_{case} = 25^{\circ}C$			-4.6	V
t <sub>rr</sub>	Reverse Recovery Time	$I_F = -11A$ , $dI_F / dt = 100A/\mu s$ $T_j = 25^{\circ}C$		270		ns
Q <sub>rr</sub>	Reverse Recovery Charge	$I_F = -11A$ , $dI_F / dt = 100A/\mu s$ $T_j = 25^{\circ}C$		2.0		μC

1) Pulse Test: Pulse Width <  $300\mu$ S, Duty Cycle  $\leq 2\%$  2) Repetitive Rating: Pulse Width limited by maximum junction temperature.

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